

## BSZ100N06LS3 G-VB Datasheet

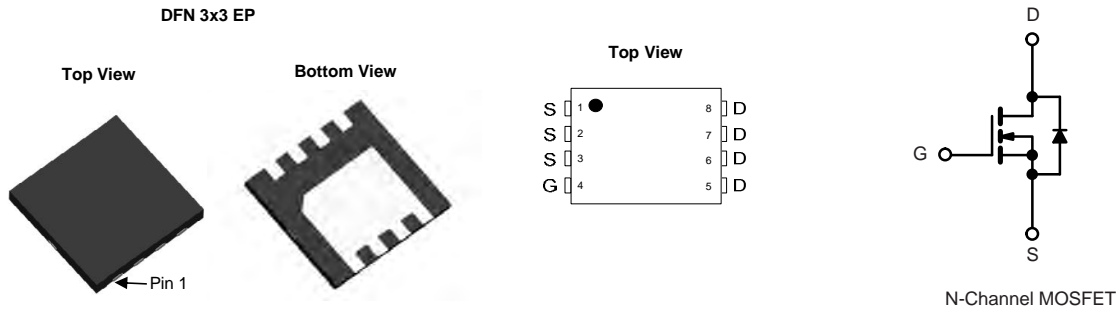
### N-Channel 60 V (D-S) MOSFET

#### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a</sup>
60	0.005 at $V_{GS} = 10$ V	30
	0.013 at $V_{GS} = 4.5$ V	26

#### FEATURES

- 175 °C Junction Temperature
- TrenchFET<sup>®</sup> Power MOSFET
- Material categorization:


**RoHS**  
 COMPLIANT


#### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current ( $T_J = 175$ °C) <sup>b</sup>	$T_C = 25$ °C	$I_D$	30	A
	$T_C = 100$ °C		25 <sup>a</sup>	
Pulsed Drain Current		$I_{DM}$	100	
Continuous Source Current (Diode Conduction)		$I_S$	70 <sup>a</sup>	
Avalanche Current		$I_{AS}$	50	
Single Avalanche Energy (Duty Cycle $\leq 1$ %)	$L = 0.1$ mH	$E_{AS}$	125	mJ
Maximum Power Dissipation	$T_C = 25$ °C	$P_D$	136	W
	$T_A = 25$ °C		3 <sup>b</sup> , 8.3 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	- 55 to 175	°C

#### THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 10$ sec	$R_{thJA}$	15	18	°C/W
	Steady State		40	50	
Maximum Junction-to-Case		$R_{thJC}$	0.85	1.1	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

 c.  $t \leq 10$  s.

**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	60			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1	2	3	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	60			A
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.005		Ω
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C		0.010		
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C		0.015		
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 15 A		0.013		
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		60		S
Dynamic						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		2650		pF
Output Capacitance	C <sub>oss</sub>			470		
Reverse Transfer Capacitance	C <sub>rss</sub>			225		
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 50 A		47	70	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			10		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			12		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 30 V, R <sub>L</sub> = 0.6 Ω I <sub>D</sub> ≅ 50 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 2.5 Ω		10	20	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			15	25	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			35	50	
Fall Time <sup>c</sup>	t <sub>f</sub>			20	30	
Source-Drain Diode Ratings and Characteristics (T <sub>C</sub> = 25 °C)						
Pulsed Current	I <sub>SM</sub>				60	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		1	1.5	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20 A, di/dt = 100 A/μs		45	100	ns

Notes:

- a. For design aid only; not subject to production testing.  
 b. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS (25 °C unless noted)



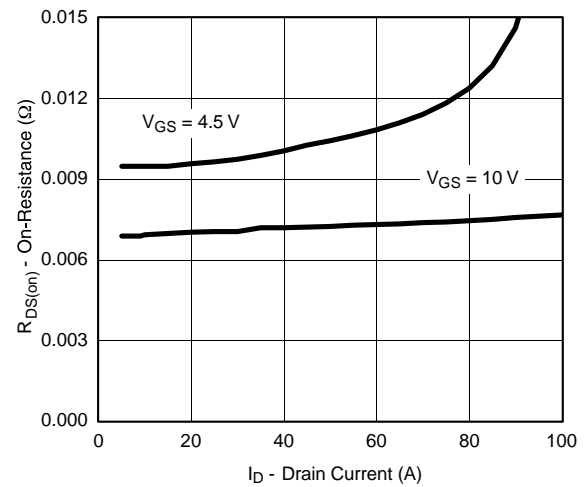
Output Characteristics



Transfer Characteristics



Transconductance



On-Resistance vs. Drain Current

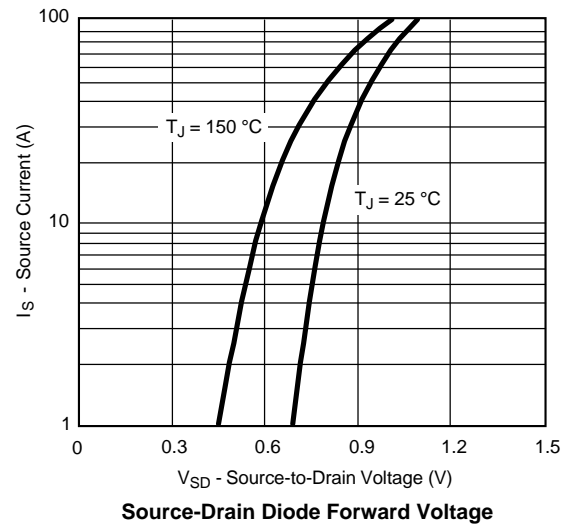
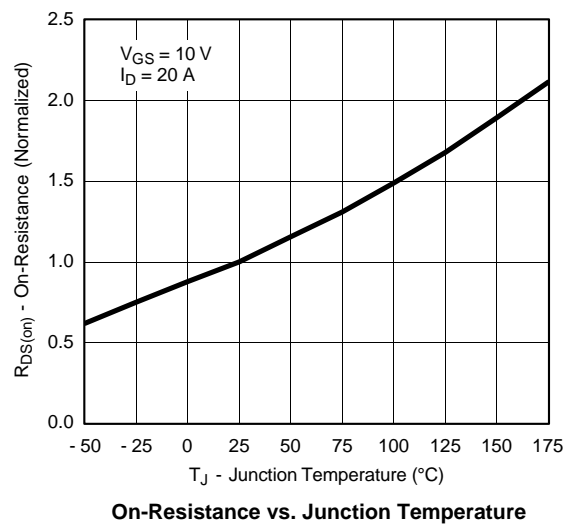


Capacitance



Gate Charge

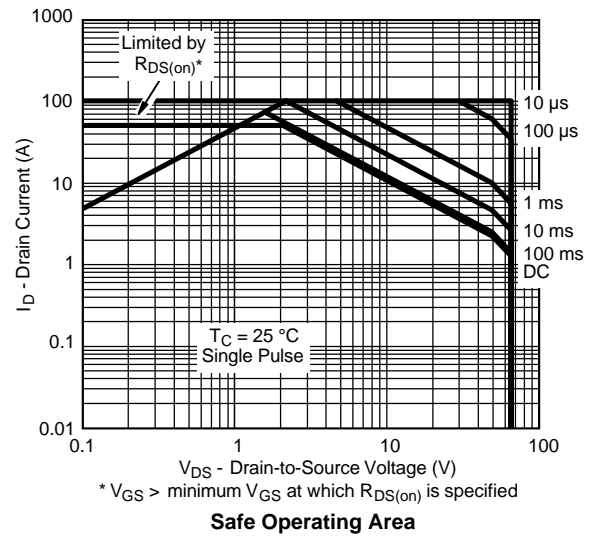
**TYPICAL CHARACTERISTICS** (25 °C unless noted)



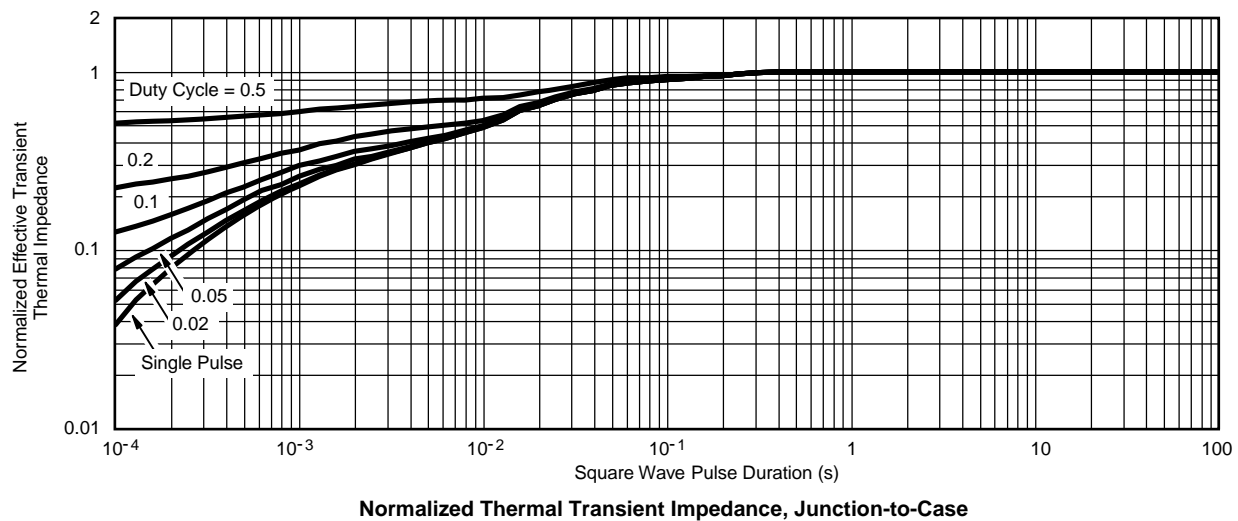
## THERMAL RATINGS



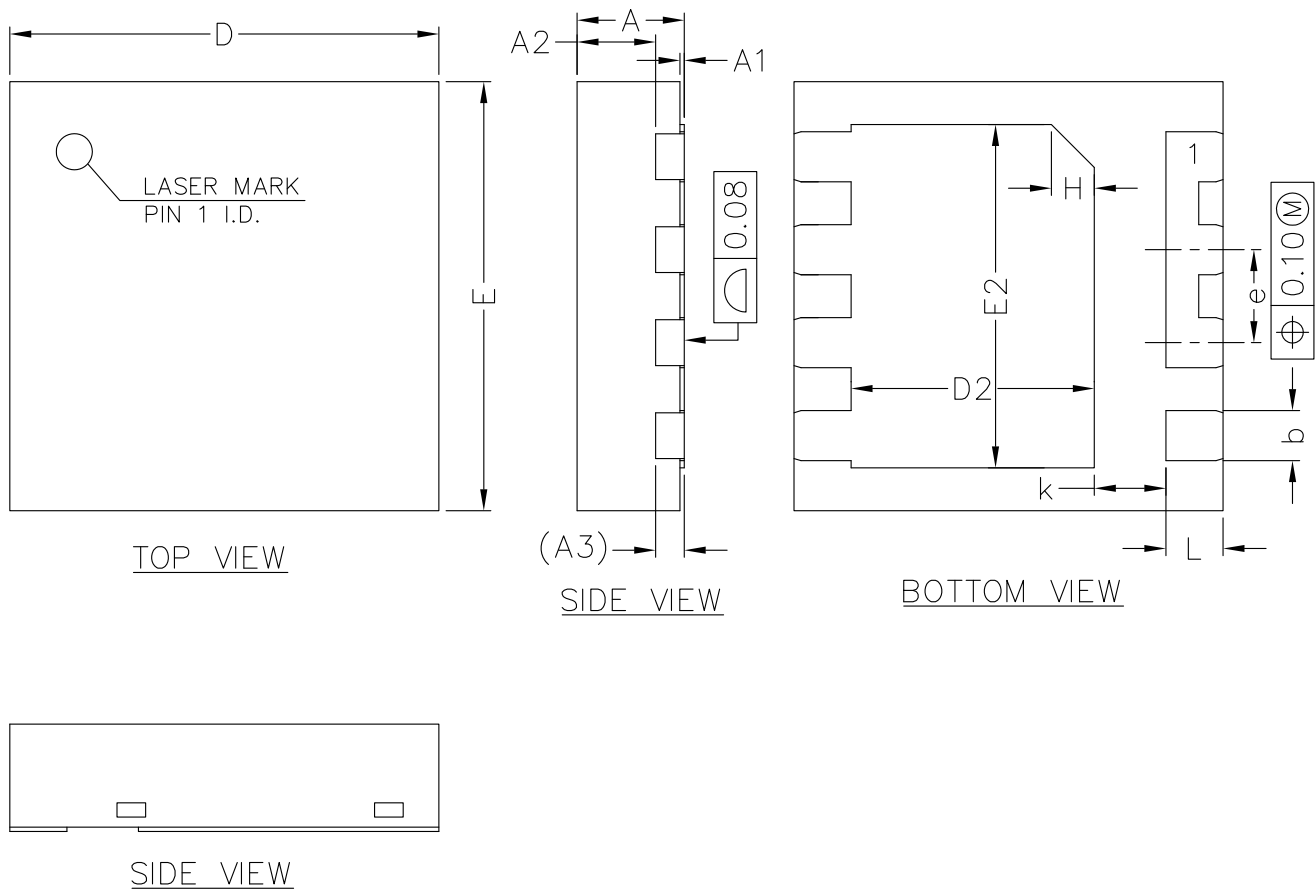
Maximum Drain Current vs. Ambient Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case



COMMON DIMENSIONS  
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A2	0.50	0.55	0.60
A3	0.20REF		
b	0.30	0.35	0.40
D	2.90	3.00	3.10
E	2.90	3.00	3.10
D2	1.60	1.70	1.80
E2	2.30	2.40	2.50
e	0.55	0.65	0.75
K	0.40	0.50	0.60
L	0.35	0.40	0.45

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